

UMBF170

Power MOSFET

N-CHANNEL ENHANCEMENT MODE

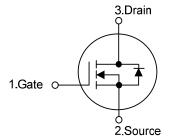
DESCRIPTION

The UMBF170 uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

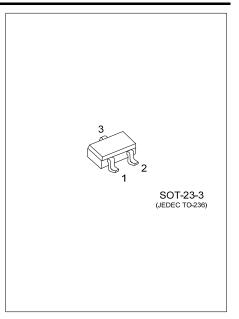
- * $R_{DS(ON)} \le 5.0\Omega$ @ V_{GS}=10V, I_D=300mA
- * $R_{DS(ON)} \le 5.3\Omega$ @ V_{GS} =4.5V, I_D =75mA
- * Low Reverse Transfer Capacitance (C_{RSS} = typical 7.5 pF)
- * Fast Switching Capability
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



ORDERING INFORMATION

| Ordering Number | | Backago | Pin Assignment | | | Packing |
|---|--|---|----------------|--------------------|-----------|-----------|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing |
| UMBF170L-AE2-R | UMBF170G-AE2-R | SOT-23-3 | G | S | D | Tape Reel |
| Note: Pin Assignment: G: Ga | te S: Source D: Drain | | | | | |
| UMBF170G-AE2-R | (1)Packing Type (2)Package Type (3)Green Package | (1) R: Tape Reel (2) AE2: SOT-23-3 (3) G: Halogen Fre | | _ead Fre | ee, L: Lo | ead Free |
| (3) Green Package (3) G: Halogen Free and Lead Free, L: Lead Free MARKING HOL L: Lead Free G: Halogen Free Www.unisonic.com.tw Copyright @ 2012 Unisonic Technologies Co. Ltd | | | | | | |
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of 3 91.C

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---|------------------|------------|------|
| Drain-Source Voltage | V _{DSS} | 60 | V |
| Drain-Gate Voltage ($R_G=25K\Omega$) | V _{DGS} | 60 | V |
| Gate-Source Voltage | V _{GSS} | ±20 | V |
| Continuous Drain Current (V _{GS} =10V) | ID | 300 | mA |
| Peak Drain Current (t _P ≦10µs) | I _{DM} | 1.2 | А |
| Power Dissipation | PD | 0.83 | W |
| Junction Temperature | TJ | +150 | °C |
| Storage Temperature | T _{STG} | -65 ~ +150 | С° |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL CHARACTERISTICS

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|-----------------|---------|------|
| Junction to Ambient | θ _{JA} | 350 | K/W |

ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

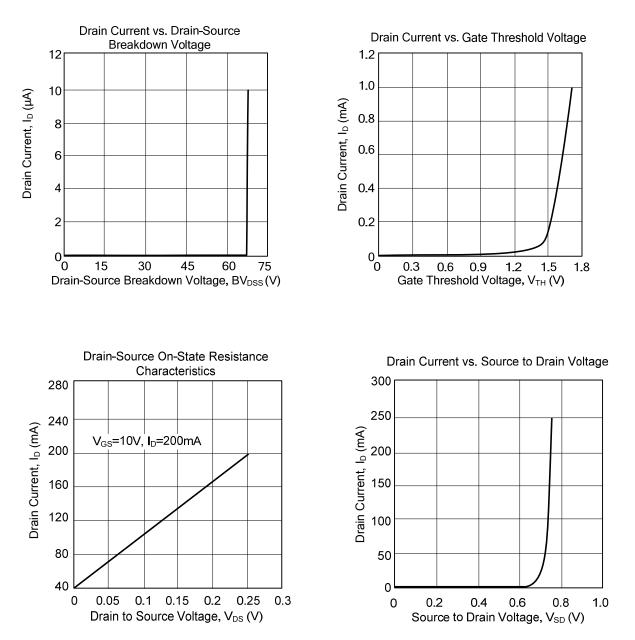
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT | |
|---|---|---|-----|------|-----|------|--|
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0 V, I _D =10µA | 60 | 75 | | V | |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =48V, V _{GS} =0V | | 0.01 | 1.0 | μA | |
| | | V _{DS} =25V, V _{GS} =0V | | 5 | 500 | nA | |
| Gate-Source Leakage Current | I _{GSS} | V_{GS} = ±15V, V_{DS} =0V | | 10 | 100 | nA | |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | nreshold Voltage V _{GS(TH)} V _{DS} =V _{GS} , I _D =1mA | | 1 | 2 | | V | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =300mA | | 2.8 | 5.0 | Ω | |
| Static Drain-Source On-Resistance | | V _{GS} =4.5V, I _D =75mA | | 3.8 | 5.3 | Ω | |
| Forward Transconductance | g fs | V _{DS} =10V, I _D =200mA 1 | | 300 | | mS | |
| DYNAMIC PARAMETERS | | | | | | | |
| Input Capacitance | CISS | | | 25 | 40 | рF | |
| Output Capacitance | C _{OSS} | V _{DS} =10 V, V _{GS} =0 V, f=1MHz | | 18 | 30 | рF | |
| Reverse Transfer Capacitance | C _{RSS} |] | | 7.5 | 10 | рF | |
| SWITCHING PARAMETERS | | | | | | | |
| Turn-ON Delay Time | t _{D(ON)} | V_{DD} =50V, V_{GS} =10V, R_{GS} =50 Ω | | 3 | 10 | ns | |
| Turn-OFF Delay Time | t _{D(OFF)} | R _G =50Ω, R _D =250Ω | | 12 | 15 | ns | |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | | |
| Maximum Body-Diode Continuous Current | ls | | | | 300 | mA | |
| Peak Source (Diode Forward) Current | I _{SM} | pulsed; $t_P \leq 10 \mu s$ | | | 1.2 | А | |
| Diode Forward Voltage | V_{SD} | I _S =300mA, V _{GS} =0V | | 0.85 | 1.5 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | I _S =300mA, dI/dt=-100A/μs, | | 30 | | ns | |
| Body Diode Reverse Recovery Charge | Qrr | V _{GS} =0V, V _{DS} =25V | | 30 | | nC | |

UNISONIC TECHINOLOGIES CO., LTD



UMBF170

TYPICAL CHARACTERISTICS



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